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Moriyama et al.

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(54) **SOLID-STATE IMAGING DEVICE AND METHOD OF MANUFACTURING THE SAME**

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(Continued)

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CPC **H01L 27/307** (2013.01); **H01L 21/265** (2013.01); **H01L 27/14612** (2013.01); **H01L 27/14665** (2013.01); **H01L 27/14687** (2013.01);
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(58) **Field of Classification Search**

CPC H01L 27/307; H01L 27/14612; H01L 27/14665; H01L 27/14687; H01L 21/265
See application file for complete search history.

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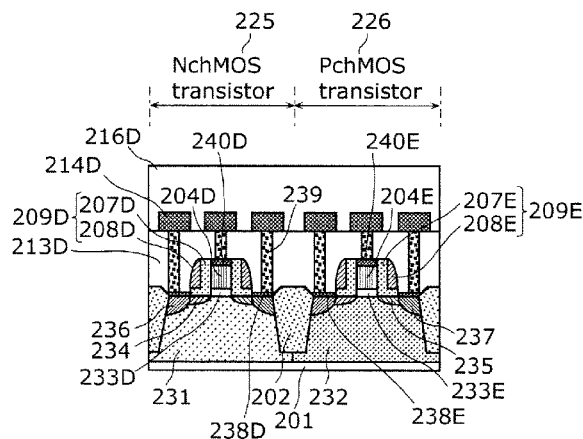
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(57) **ABSTRACT**

A solid-state imaging device includes: a semiconductor substrate; a pixel unit formed on the semiconductor substrate; and a peripheral circuit unit formed on the semiconductor substrate, at a periphery of the pixel unit, in which the pixel unit includes: a photoelectric conversion film which converts incident light into charges; and a floating diffusion which holds the charges, the peripheral circuit unit includes a transistor including a gate electrode and two source and drain diffusion regions, and the two source and drain diffusion regions have a higher impurity concentration than an impurity concentration of the floating diffusion.

18 Claims, 11 Drawing Sheets



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H01L 21/265 (2006.01)
H01L 29/423 (2006.01)
H01L 21/324 (2006.01)
- (52) **U.S. Cl.**
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21/324 (2013.01)
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FIG. 1

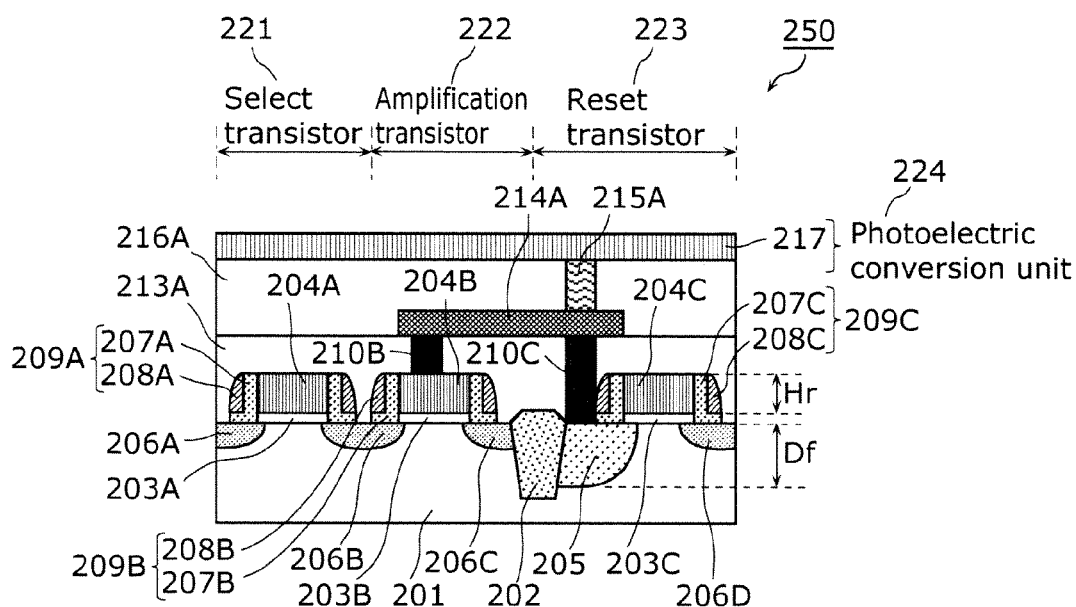


FIG. 2

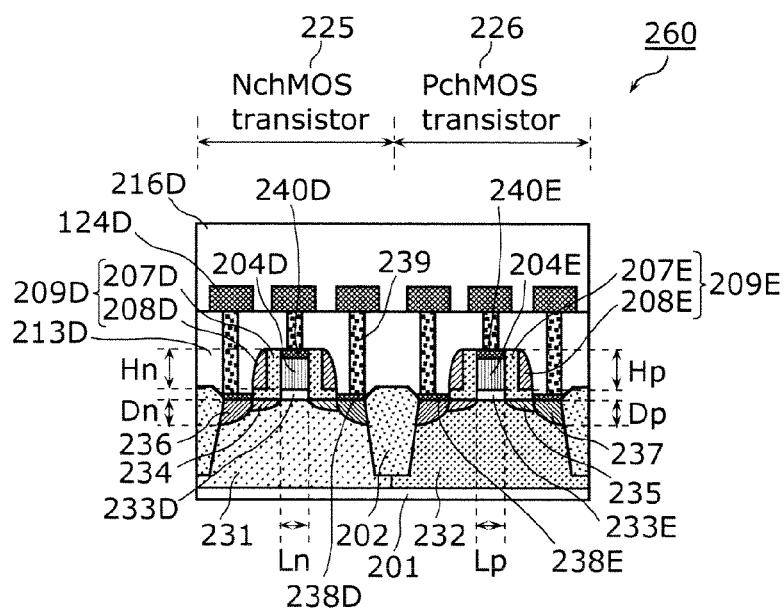


FIG. 3

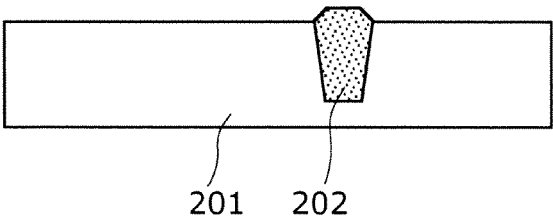


FIG. 4

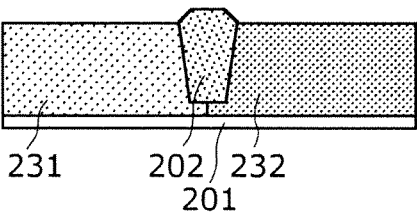


FIG. 5

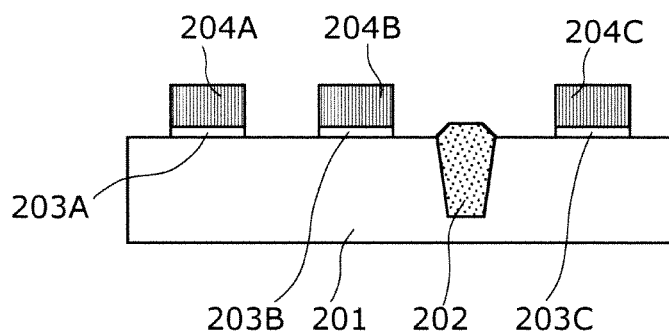


FIG. 6

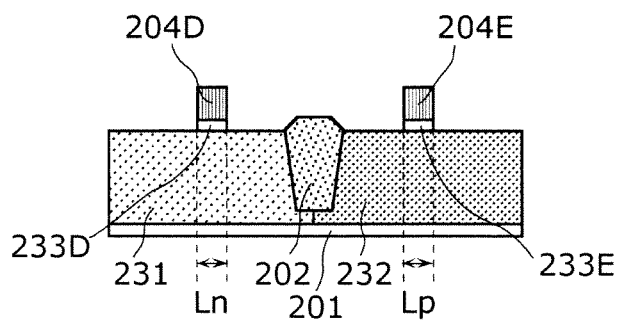


FIG. 7

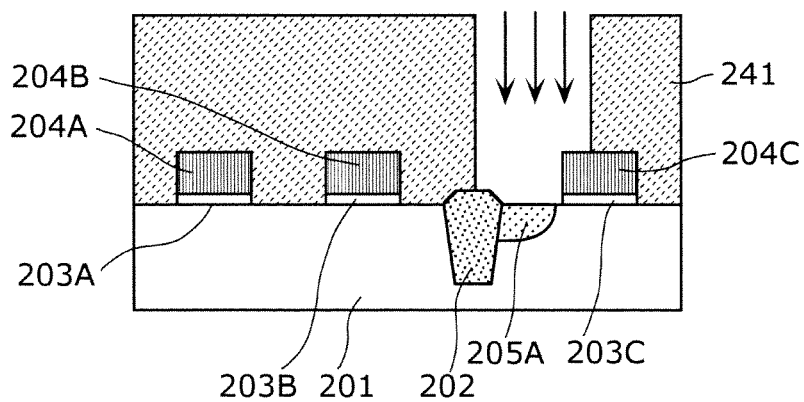


FIG. 8

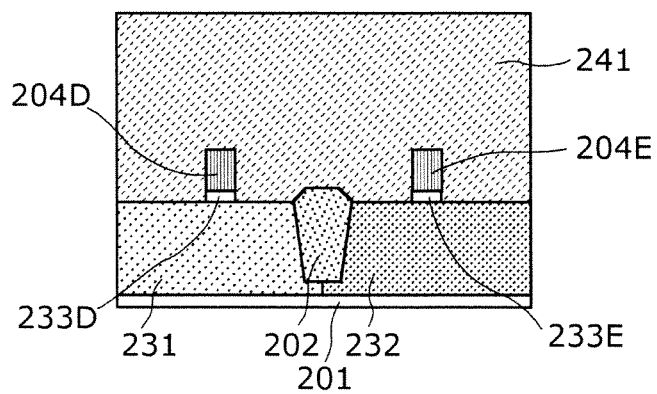


FIG. 9

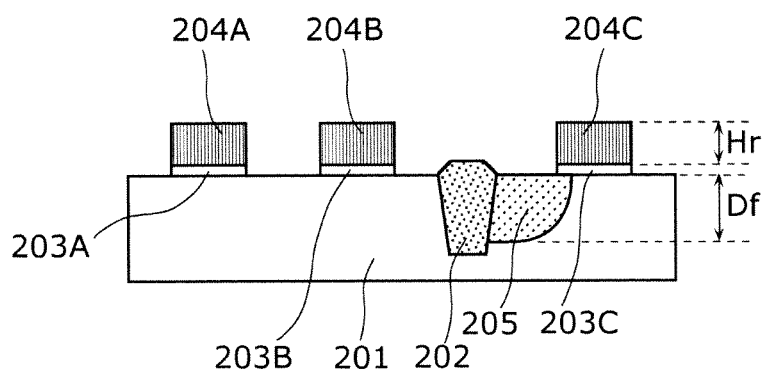


FIG. 10

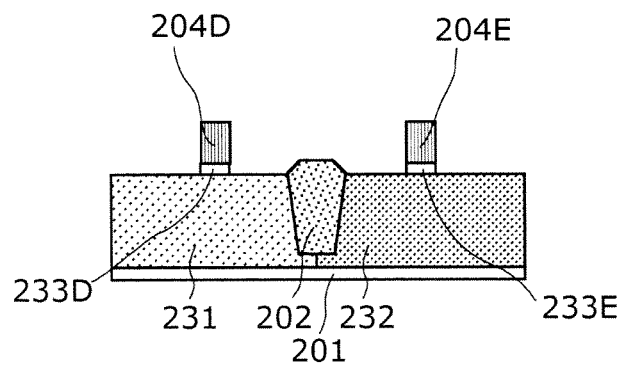


FIG. 11

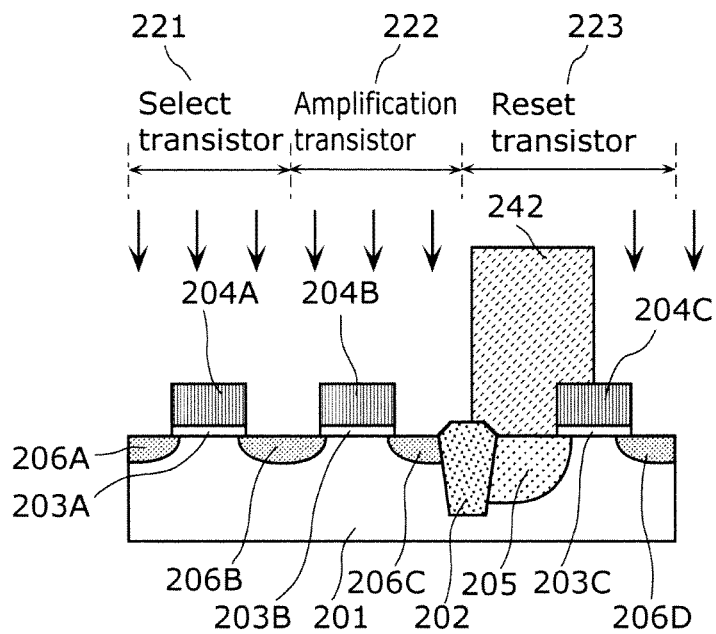


FIG. 12

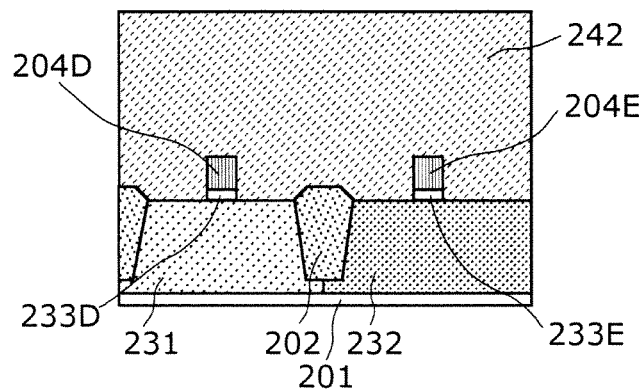


FIG. 13

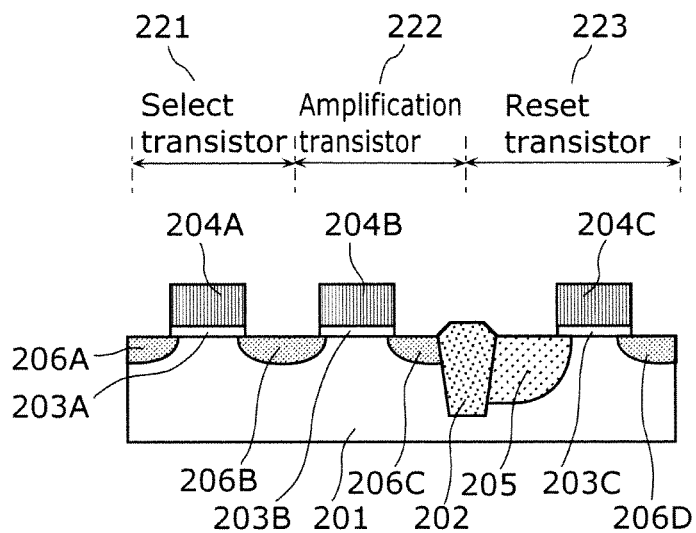


FIG. 14

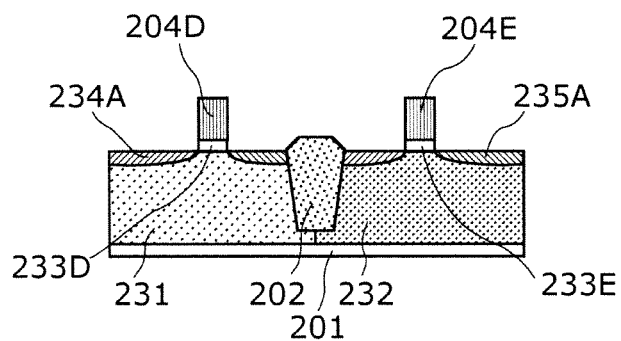


FIG. 15

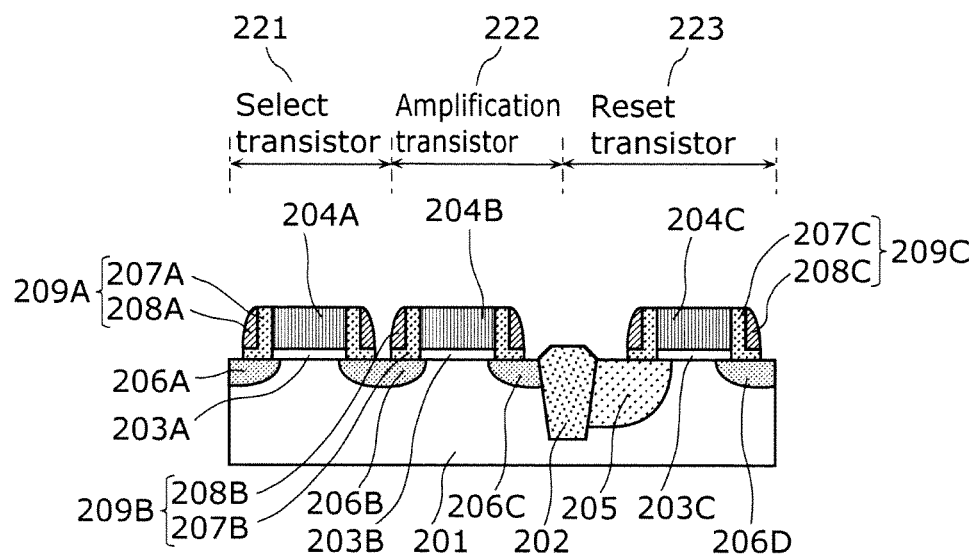


FIG. 16

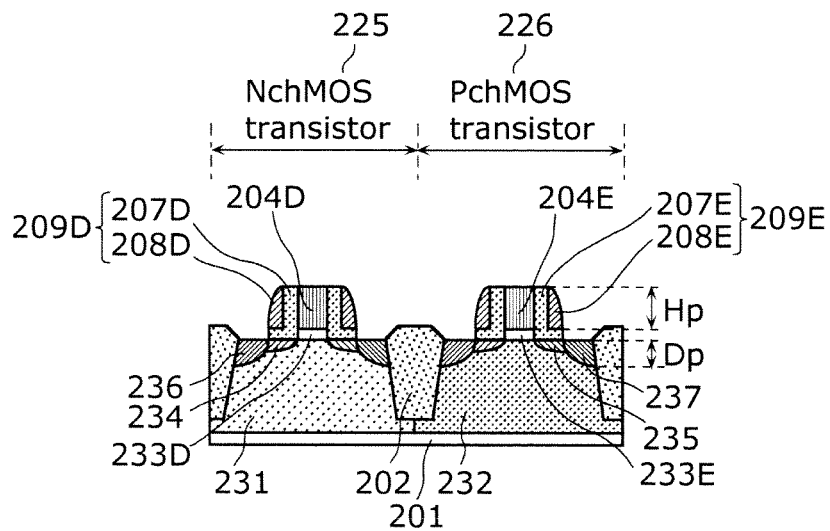


FIG. 17

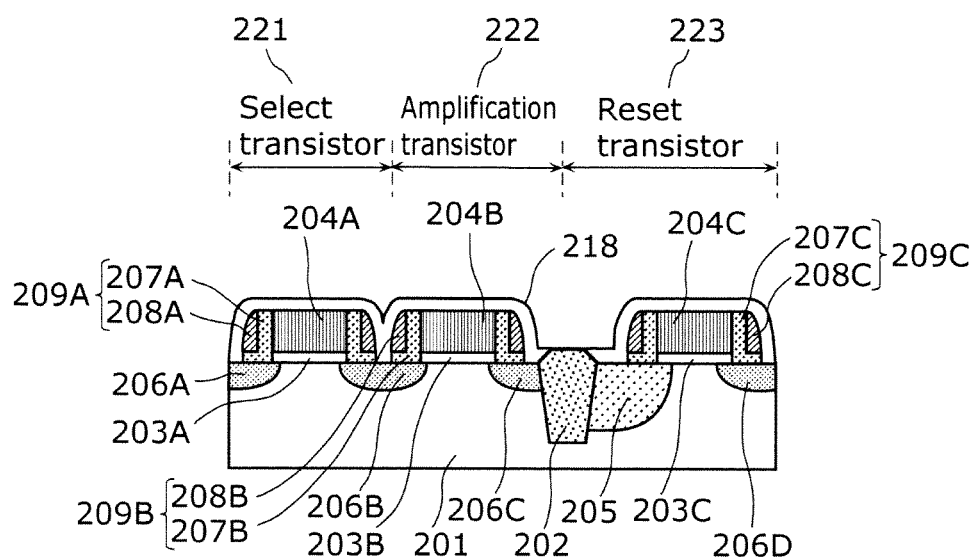


FIG. 18

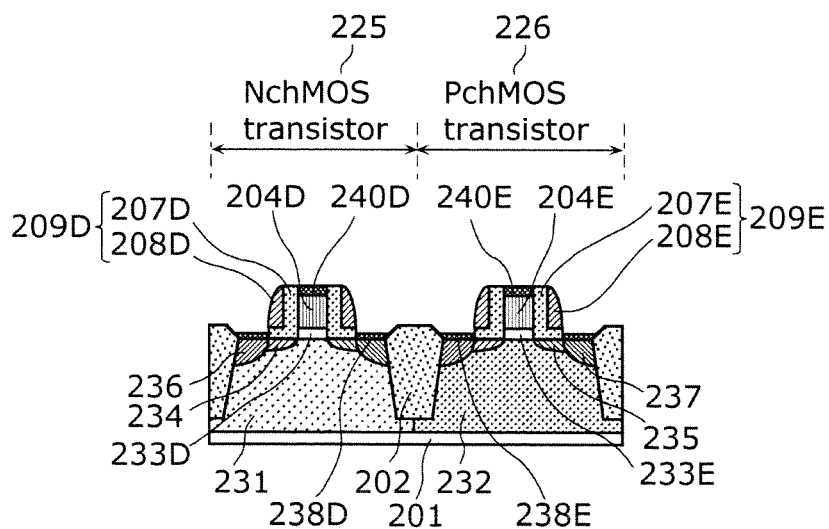


FIG. 19

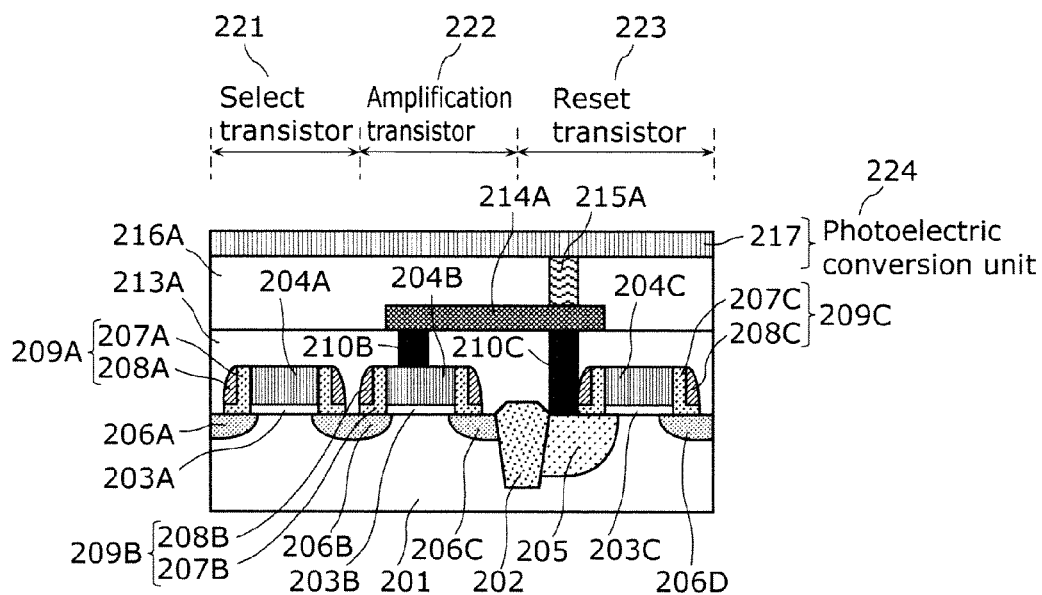


FIG. 20

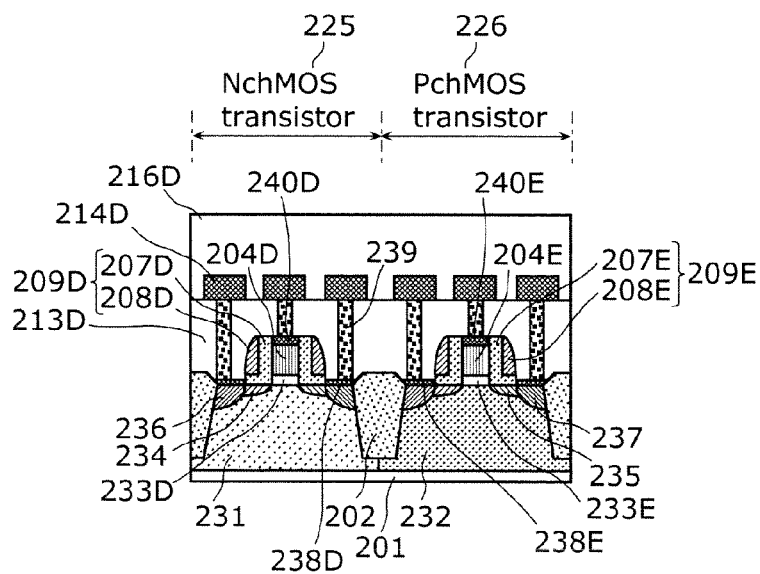


FIG. 21

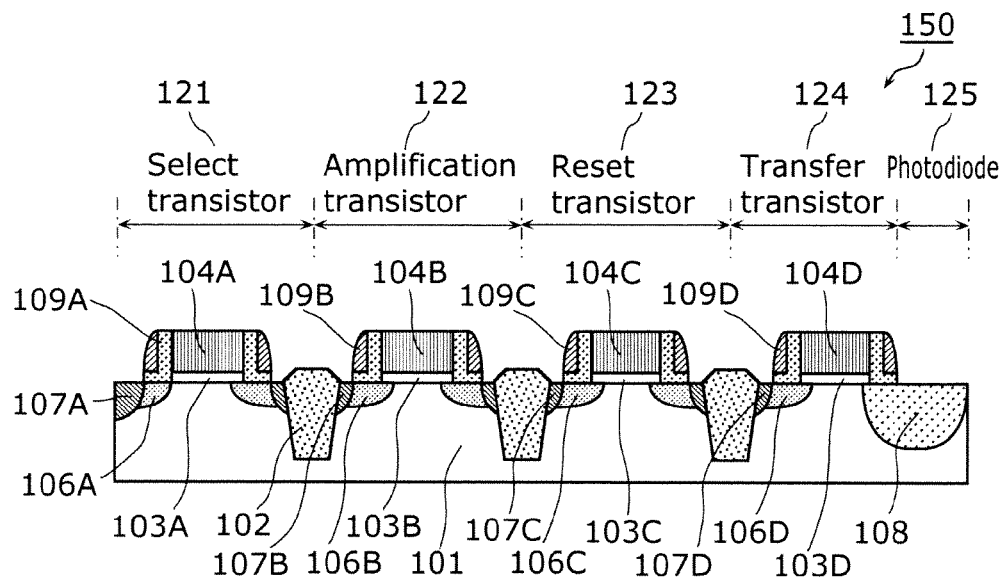
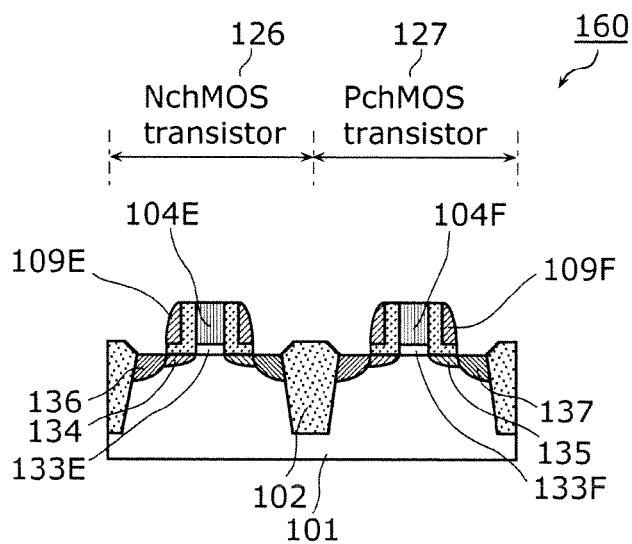


FIG. 22



SOLID-STATE IMAGING DEVICE AND METHOD OF MANUFACTURING THE SAME

CROSS REFERENCE TO RELATED APPLICATIONS

This is a continuation application of PCT International Application No. PCT/JP2013/003489 filed on Jun. 3, 2013, designating the United States of America, which is based on and claims priority of Japanese Patent Application No. 2012-145946 filed on Jun. 28, 2012. The entire disclosures of the above-identified applications, including the specifications, drawings and claims are incorporated herein by reference in their entirety.

FIELD

The present disclosure relates to a solid-state imaging device and a method of manufacturing the solid-state imaging device.

BACKGROUND

A metal oxide semiconductor (MOS) image sensor includes a pixel unit formed on a semiconductor substrate and including a photoelectric conversion unit for converting incident light into an electric signal and a peripheral circuit unit formed at the periphery of the pixel unit. In a solid-state imaging device such as the MOS image sensor, a demand for the peripheral circuit unit to operate at a high speed has been increasing in recent years. In accordance with this trend, a demand for the miniaturization of a MOS transistor included in the peripheral circuit unit has been increasing (e.g., Patent Literature 1 (PTL 1)).

Moreover, Patent Literature 2 (PTL 2) suggests a new image sensor (stacked image sensor) including a photoelectric conversion element (a photoelectric conversion film) formed on wiring rather than on a silicon substrate.

CITATION LIST

Patent Literature

- [PTL 1] Japanese Unexamined Patent Application Publication No. 2010-056515
[PTL 2] Japanese Unexamined Patent Application Publication No. 2012-019169

SUMMARY

Technical Problem

The following describes a configuration of a solid-state imaging device. FIG. 21 is a cross-sectional view of a pixel unit 150 included in the solid-state imaging device. The pixel unit 150 includes a select transistor 121, an amplification transistor 122, a reset transistor 123, a transfer transistor 124, and a photodiode 125. The select transistor 121, the amplification transistor 122, the reset transistor 123, and the transfer transistor 124 are separated by element isolation regions 102 formed on the surface of a semiconductor substrate 101.

FIG. 22 is a cross-sectional view of a peripheral circuit unit 160 included in the solid-state imaging device. The peripheral circuit unit 160 includes an NchMOS transistor 126 and a PchMOS transistor 127. The NchMOS transistor 126 and the

PchMOS transistor 127 are separated by the element isolation region 102 formed on the surface of the semiconductor substrate 101.

The select transistor 121 illustrated in FIG. 21 includes a gate insulating film 103A, a gate electrode 104A, sidewalls 109A, two N-type lightly doped drain (LDD) diffusion regions 106A, and two N-type source and drain diffusion regions 107A. Here, the gate insulating film 103A is formed on the semiconductor substrate 101. The gate electrode 104A is formed on the gate insulating film 103A. The sidewalls 109A are formed on the side faces of the gate electrode 104A. The two N-type LDD diffusion regions 106A and the two N-type source and drain diffusion regions 107A are formed on the surface of the semiconductor substrate 101. Moreover, the two N-type LDD diffusion regions 106A are formed on opposite sides of the gate electrode 104A. The N-type source and drain diffusion regions 107A are formed one on either side of the sidewalls 109A sandwiching the gate electrode 104A.

The amplification transistor 122 includes a gate insulating film 103B, a gate electrode 104B, sidewalls 109B, two N-type LDD layers 106B, and two N-type source and drain diffusion regions 107B. Here, the gate insulating film 103B is formed on the semiconductor substrate 101. The gate electrode 104B is formed on the gate insulating film 103B. The sidewalls 109B are formed on the side faces of the gate electrode 104B. The two N-type LDD diffusion regions 106B and the two N-type source and drain diffusion regions 107B are formed on the surface of the semiconductor substrate 101. Moreover, the two N-type LDD diffusion regions 106B are formed on opposite sides of the gate electrode 104B. The two N-type source and drain diffusion regions 107B are formed one on either side of the sidewalls 109B sandwiching the gate electrode 104B.

The reset transistor 123 includes a gate insulating film 103C, a gate electrode 104C, sidewalls 109C, two N-type LDD diffusion regions 106C, and two N-type source and drain diffusion regions 107C. Here, the gate insulating film 103C is formed on the semiconductor substrate 101. The gate electrode 104C is formed on the gate insulating film 103C. The sidewalls 109C are formed on the side faces of the gate electrode 104C. The two N-type LDD diffusion regions 106C and the two N-type source and drain diffusion regions 107C are formed on the surface of the semiconductor substrate 101. Moreover, the two N-type LDD diffusion regions 106C are formed on opposite sides of the gate electrode 104C. The two N-type source and drain diffusion regions 107C are formed one on either side of the sidewalls 109C sandwiching the gate electrode 104C.

The transfer transistor 124 includes a gate insulating film 103D, a gate electrode 104D, sidewalls 109D, an N-type LDD diffusion region 106D, an N-type source and drain diffusion region 107D, and an N-type buried diffusion region 108. The gate insulating film 103D is formed on the semiconductor substrate 101. The gate electrode 104D is formed on the gate insulating film 103D. The sidewalls 109D are formed on the side faces of the gate electrode 104D. The N-type LDD diffusion region 106D is formed on one side of the gate electrode 104D. The N-type source and drain diffusion region 107D is formed on either side of the sidewalls 109D. The N-type buried diffusion region 108 is formed on the opposite side of the gate electrode 104D. It should be noted that the N-type buried diffusion region 108 also functions as the photodiode 125. Moreover, the N-type LDD diffusion region 106D, the N-type source and drain diffusion region 107D, and an N-type buried diffusion region 108 are formed on the surface of the semiconductor substrate 101.

Here, the photodiode **125** is a photoelectric conversion unit for converting incident light into an electric signal (charges). Moreover, the N-LDD diffusion regions **106C**, the N-type source and drain diffusion regions **107C**, the N-LDD diffusion region **106D**, and the N-type source and drain diffusion region **107D** function as floating diffusions which hold charges generated in the photodiode **125** and transferred via the transfer transistor **124**.

The NchMOS transistor **126** illustrated in FIG. 22 includes a gate insulating film **133E**, a gate electrode **104E**, sidewalls **109E**, two N-type extension diffusion regions **134**, and two N-type source and drain diffusion regions **136**. Here, the gate insulating film **133E** is formed on the semiconductor substrate **101**. The gate electrode is formed on the gate insulating film **133E**. The sidewalls **109E** are formed on the side faces of the gate electrode **104E**. The two N-type extension diffusion regions **134** and the two N-type source and drain diffusion regions **136** are formed on the surface of the semiconductor substrate **101**. Moreover, the two N-type extension diffusion regions **134** are formed on opposite sides of the gate electrode **104E**. The two N-type source and drain diffusion regions **136** are formed one on either side of the sidewalls **109E** sandwiching the gate electrode **104E**.

The PchMOS transistor **127** includes a gate insulating film **133F**, a gate electrode **104F**, sidewalls **109F**, two P-type extension diffusion regions **135**, and two P-type source and drain diffusion regions **137**. Here, the gate insulating film **133F** is formed on the semiconductor substrate **101**. The gate electrode **104F** is formed on the gate insulating film **133F**. The sidewalls **109F** are formed on the side faces of the gate electrode **104F**. The two P-type extension diffusion regions **135** and the two P-type source and drain diffusion regions **137** are formed on the surface of the semiconductor substrate **101**. Moreover, the two P-type extension diffusion regions **135** are formed on opposite sides of the gate electrode **104F**. The two P-type source and drain diffusion regions **137** are formed one on either side of the sidewalls **109F** sandwiching the gate electrode **104F**.

In a method of manufacturing the solid-state imaging device described above, the element isolation regions **102** are formed on the surface of the semiconductor substrate **101**. The N-type buried diffusion region **108** in the photodiode **125** is formed in the pixel unit **150** by ion implantation.

A gate oxide film is formed in the pixel unit **150** and the peripheral circuit unit **160**. A film of a gate electrode material is formed in the pixel unit **150** and the peripheral circuit unit **160**. By patterning the gate oxide film, the gate insulating film, and the film of a gate electrode material into desired shapes, the gate insulating films **103A**, **103B**, **103C**, and **103D** and the gate electrodes **104A**, **104B**, **104C**, and **104D** are formed in the pixel unit **150**, and the gate insulating films **133E** and **133F** and the gate electrodes **104E** and **104F** are formed in the peripheral circuit unit **160**.

The N-type extension diffusion regions **134** are selectively formed by the ion implantation on the surface of the semiconductor substrate **101** in the peripheral circuit unit **160**.

The N-type LDD diffusion regions **106A**, **106B**, **106C**, and **106D** are selectively formed by the ion implantation on the surface of the semiconductor substrate **101** in the pixel unit **150**.

The P-type extension diffusion regions **135** are selectively formed by the ion implantation on the surface of the semiconductor substrate **101** in the peripheral circuit unit **160**.

The sidewalls **109A** to **109F** are formed on the side faces of the gate electrodes **104A** to **104F**, respectively.

The N-type source and drain diffusion regions **136** are selectively formed by the ion implantation on the surface of the semiconductor substrate **101** in the peripheral circuit unit **160**.

The N-type source and drain diffusion regions **107A**, **107B**, **107C**, and **107D** are selectively formed by the ion implantation on the surface of the semiconductor substrate **101** in the pixel unit **150**.

The P-type source and drain diffusion regions **137** are selectively formed by the ion implantation on the surface of the semiconductor substrate **101** in the peripheral circuit unit **160**.

To activate impurities in the diffusion regions, a heat treatment is performed at a temperature range of 800° C. to 1000° C. using a lamp annealing apparatus. Here, the use of the lamp annealing apparatus allows the heat treatment in a short period of time to activate the impurities. This can suppress thermal diffusion of the diffusion regions. That is, the gate lengths of the NchMOS transistor **126** and the PchMOS transistor **127** can be decreased by suppressing the thermal diffusion of the N-type extension diffusion regions **134** and P-type extension diffusion regions **135** in the peripheral circuit unit **160**. This allows the transistors included in the peripheral circuit unit **160** to be miniaturized.

However, in the solid-state imaging device illustrated in FIGS. 21 and 22, the impurity concentrations of the N-type source and drain diffusion regions **107A**, **107B**, **107C**, and **107D** in the pixel unit **150** need to be high (e.g., a concentration of at least 10^{20} cm^{-3}). Thus, defects are caused on the surface of the semiconductor substrate **101** due to damage caused by the ion implantation.

Moreover, if the heat treatment is performed using the lamp annealing apparatus to activate these diffusion regions, the defects on the surface of the semiconductor substrate **101** cannot be fully repaired. This means that, in particular, defects in the N-type source and drain diffusion regions **107C** and the N-type source and drain diffusion region **107D**, which function as floating diffusions, become leak current sources, thereby deteriorating pixel characteristics.

Moreover, for instance, the following introduces the case where a technology disclosed in PTL 1 is applied to the stacked image sensor disclosed in PTL 2. In this case, an impurity diffusion region having a high impurity concentration is formed by the ion implantation in an N-type source and drain diffusion region in a pixel unit. Subsequently, to prevent damage due to the ion implantation, a high-temperature sintering treatment (for example, at a temperature of 400° C. or above) is performed after a photoelectric conversion film is formed. In this case, degradation of the photoelectric conversion characteristics of a layered film is a problem.

Solution to Problem

A solid-state imaging device according to an aspect of the present disclosure includes: a semiconductor substrate; a pixel unit formed on the semiconductor substrate; and a peripheral circuit unit formed on the semiconductor substrate, at a periphery of the pixel unit, in which the pixel unit includes: a photoelectric conversion film which converts incident light into charges; and a floating diffusion which holds the charges, the peripheral circuit unit includes a transistor including a gate electrode and two source and drain diffusion regions, and the two source and drain diffusion regions have a higher impurity concentration than an impurity concentration of the floating diffusion.

Additional benefits and advantages of the disclosed embodiments will be apparent from the Specification and

Drawings. The benefits and/or advantages may be individually obtained by the various embodiments and features of the Specification and Drawings, which need not all be provided in order to obtain one or more of such benefits and/or advantages.

BRIEF DESCRIPTION OF DRAWINGS

These and other advantages and features will become apparent from the following description thereof taken in conjunction with the accompanying Drawings, by way of non-limiting examples of embodiments disclosed herein.

FIG. 1 is a cross-sectional view of a pixel unit of a solid-state imaging device according to the embodiment.

FIG. 2 is a cross-sectional view of a peripheral circuit unit of the solid-state imaging device according to the embodiment.

FIG. 3 is a cross-sectional view of the pixel unit in a manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 4 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 5 is a cross-sectional view of the pixel unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 6 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 7 is a cross-sectional view of the pixel unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 8 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 9 is a cross-sectional view of the pixel unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 10 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 11 is a cross-sectional view of the pixel unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 12 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 13 is a cross-sectional view of the pixel unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 14 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 15 is a cross-sectional view of the pixel unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 16 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 17 is a cross-sectional view of the pixel unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 18 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 19 is a cross-sectional view of the pixel unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 20 is a cross-sectional view of the peripheral circuit unit in the manufacturing process of the solid-state imaging device according to the embodiment.

FIG. 21 is a cross-sectional view of the pixel unit of a solid-state imaging device.

FIG. 22 is a cross-sectional view of the peripheral circuit unit of the solid-state imaging device.

DESCRIPTION OF EMBODIMENT

A solid-state imaging device according to an aspect of the present disclosure includes: a semiconductor substrate; a pixel unit formed on the semiconductor substrate; and a peripheral circuit unit formed on the semiconductor substrate, at a periphery of the pixel unit, in which the pixel unit includes: a photoelectric conversion film which converts incident light into charges; and a floating diffusion which holds the charges, the peripheral circuit unit includes a transistor including a gate electrode and two source and drain diffusion regions, and the two source and drain diffusion regions have a higher impurity concentration than an impurity concentration of the floating diffusion.

This configuration allows the solid-state imaging device according to an aspect of the present disclosure to suppress the expansion of the source and drain diffusion regions in the transistor of the peripheral circuit unit. This can decrease the gate length of the transistor of the peripheral circuit unit. Moreover, the solid-state imaging device can repair defects on the surface of the semiconductor substrate due to damage caused by ion implantation to form a floating diffusion in the pixel unit. Thus, in the solid-state imaging device, it is possible to achieve both of the miniaturization of the transistor included in the peripheral circuit unit and the reduction of defects due to damage caused by the ion implantation to form the floating diffusion in the pixel unit.

Moreover, depths of the two source and drain diffusion regions may be at most a height of the gate electrode.

This configuration means that the expansion of the source and drain diffusion regions is suppressed. Thus, the gate length of the transistor of the peripheral circuit unit can be decreased.

Moreover, a depth of the floating diffusion may be at least a height of the gate electrode.

The configuration means that the floating diffusion is sufficiently diffused. Thus, gradual expansion of the floating diffusion can suppress a leakage current in PN junction. This can improve the sensitivity of a pixel.

Moreover, the two source and drain diffusion regions may have an impurity concentration of at least $1 \times 10^{20} \text{ cm}^{-3}$.

According to this configuration, the source and drain diffusion regions have low resistance. Thus, the driving capability of the transistor can be improved.

Moreover, the floating diffusion may have an impurity concentration of at most $1 \times 10^{19} \text{ cm}^{-3}$.

This configuration can gradually expand the floating diffusion.

Moreover, the gate electrode may have a length of 65 nm or less.

This configuration can improve the driving capability of the transistor included in the peripheral circuit unit.

Moreover, the solid-state imaging device may further include: a non-metal contact plug connected with the floating diffusion; and a line connected with the non-metal contact

plug, in which the floating diffusion and the photoelectric conversion film are connected via the non-metal contact plug and the line.

This configuration can achieve a lower contact resistance between the floating diffusion and the contact plug than the case where a contact plug of general metal such as tungsten is used.

Moreover, the photoelectric conversion film may be formed with an organic material.

A method of manufacturing a solid-state imaging device according to an aspect of the present disclosure is a method of manufacturing a solid-state imaging device which includes: a semiconductor substrate; a pixel unit formed on the semiconductor substrate; and a peripheral circuit unit formed on the semiconductor substrate, at a periphery of the pixel unit, in which the pixel unit includes: a photoelectric conversion film which converts incident light into charges; and a floating diffusion which holds the charges, and the peripheral circuit unit includes a transistor including a gate electrode and two source and drain diffusion regions. The method includes: (a) forming the gate electrode above the semiconductor substrate; (b) implanting a first impurity into the semiconductor substrate after step (a) to form the floating diffusion; (c) performing a first heat treatment after step (b); and (d) forming the two source and drain diffusion regions after step (c).

Moreover, step (d) may include: (e) implanting a second impurity into the semiconductor substrate to form diffusion regions of a low impurity concentration to be included in the two source and drain diffusion regions; (f) forming sidewalls on side faces of the gate electrode after step (e); (g) implanting a third impurity into the semiconductor substrate after step (f) to form diffusion regions of a high impurity concentration to be included in the two source and drain diffusion regions; and (h) performing a second heat treatment after step (g).

According to this, defects due to damage caused by the ion implantation can be reduced by performing the first heat treatment on the floating diffusion in the method of manufacturing of a solid-state imaging device according to an aspect of the present disclosure. Moreover, the method of manufacturing can suppress the expansion of the source and drain diffusion regions in the peripheral circuit unit by properly setting conditions for the second heat treatment. This can decrease the gate length of the transistor. Thus, the method of manufacturing can achieve both of miniaturization of the transistor included in the peripheral circuit unit and reduction of defects due to damage caused by the ion implantation to form the floating diffusion in the pixel unit.

Moreover, the first heat treatment may be performed at a temperature of 800° C. or above using a diffusion furnace.

This can repair defects on the surface of the semiconductor substrate in the pixel unit due to damage caused by the ion implantation in step (b).

Moreover, the second heat treatment may be performed at a temperature of 900° C. or above using a lamp annealing apparatus.

This can achieve both of activation and suppression of thermal diffusion of the second impurity and the third impurity implanted into the surface of the semiconductor substrate in the peripheral circuit unit. Thus, the gate length of the transistor of the peripheral circuit unit can be decreased.

Moreover, the method of manufacturing a solid-state imaging device may further include forming a non-metal contact plug to be connected with the floating diffusion, after step (h).

This can achieve a lower contact resistance between the floating diffusion and the contact plug than the case where a contact plug of general metal such as tungsten is used.

Moreover, the non-metal contact plug may be polycrystal silicon containing an impurity of a same conductivity type as the silicon impurity.

Moreover, the method of manufacturing a solid-state imaging device may further include performing a third heat treatment using a diffusion furnace after step (h), in which the third heat treatment is performed at a temperature which is at most a temperature during the first heat treatment.

This can decrease dangling bonds caused on an interface between a gate insulating film and the semiconductor substrate in the pixel unit when the lamp annealing apparatus is used in the second heat treatment. Moreover, a temperature during the third heat treatment is at most a temperature during the first heat treatment. Thus, it is possible to suppress thermal diffusion of the second impurity implanted into the surface of the semiconductor substrate in the peripheral circuit unit. This can decrease the gate length of the transistor of the peripheral circuit unit.

Moreover, the present disclosure can be achieved as a semiconductor integrated circuit (LSI) which achieves part or all of the functions of such a solid-state imaging device or as an imaging apparatus (a camera) including the solid-state imaging device.

The following describes a solid-state imaging device and a method of manufacturing the solid-state imaging device according to the present embodiment with reference to the drawings.

The exemplary embodiment described below shows a general or specific example. The numerical values, shapes, materials, structural elements, the arrangement and connection of the structural elements, steps, the processing order of the steps, and others shown in the following embodiment are mere examples, and therefore do not limit the present invention. Moreover, among the structural elements in the following embodiment, the structural elements not recited in the independent claims representing superordinate concept are described as optional structural elements.

The following describes a configuration of the solid-state imaging device according to the present embodiment.

The solid-state imaging device according to the present embodiment includes a pixel unit **250** and a peripheral circuit unit **260** formed at the periphery of the pixel unit **250**. FIG. **1** is a cross-sectional view of the pixel unit **250** of the solid-state imaging device according to the present embodiment. Moreover, FIG. **2** is a cross-sectional view of the peripheral circuit unit **260** of the solid-state imaging device according to the present embodiment.

The pixel unit **250** illustrated in FIG. **1** includes a select transistor **221**, an amplification transistor **222**, a reset transistor **223**, and a photoelectric conversion unit **224**.

Moreover, the amplification transistor **222** and the reset transistor **223** are isolated by an element isolation region **202** (a shallow trench isolation (STI) region). It should be noted that an implant isolation region may be used as the element isolation region **202** instead of the STI region.

The use of the implant isolation region can decrease a leakage current due to crystal defects on the interface between the element isolation region **202** and a semiconductor substrate **201**.

The select transistor **221** includes a gate insulating film **203A**, a gate electrode **204A**, sidewalls **209A**, an N-type diffusion region **206A**, and an N-type diffusion region **206B**. Here, the gate insulating film **203A** is formed on the semiconductor substrate **201**. The gate electrode **204A** is formed on the gate insulating film **203A**. The sidewalls **209A** are formed on the side faces of the gate electrode **204A**. The N-type diffusion region **206A** is formed on one side of the

gate electrode **204A**. The N-type diffusion region **206B** is formed on the opposite side of the gate electrode **204A**. The sidewall **209A** includes a silicon oxide film **207A** and a silicon nitride film **208A**. Moreover, the N-type diffusion region **206A** and the N-type diffusion region **206B** are formed on the surface of the semiconductor substrate **201**.

The amplification transistor **222** includes a gate insulating film **203B**, a gate electrode **204B**, sidewalls **209B**, the N-type diffusion region **206B**, and an N-type diffusion region **206C**. Here, the gate insulating film **203B** is formed on the semiconductor substrate **201**. The gate electrode **204B** is formed on the gate insulating film **203B**. The sidewalls **209B** are formed on the side faces of the gate electrode **204B**. The N-type diffusion region **206B** is formed on one side of the gate electrode **204B**. The N-type diffusion region **206C** is formed on the opposite side of the gate electrode **204B**. The sidewall **209B** includes a silicon oxide film **207B** and a silicon nitride film **208B**. Moreover, the N-type diffusion region **206B** and the N-type diffusion region **206C** are formed on the surface of the semiconductor substrate **201**.

The reset transistor **223** includes a gate insulating film **203C**, a gate electrode **204C**, sidewalls **209C**, an N-type diffusion region **205**, and an N-type diffusion region **206D**. Here, the gate insulating film **203C** is formed on the semiconductor substrate **201**. The gate electrode **204C** is formed on the gate insulating film **203C**. The sidewalls **209C** are formed on the side faces of the gate electrode **204C**. The N-type diffusion region **205** is formed on one side of the gate electrode **204C**. The N-type diffusion region **206D** is formed on the opposite side of the gate electrode **204C**. The sidewall **209C** includes a silicon oxide film **207C** and a silicon nitride film **208C**. Moreover, the N-type diffusion region **205** and the N-type diffusion region **206D** are formed on the surface of the semiconductor substrate **201**.

The photoelectric conversion unit **224** includes a photoelectric conversion film **217**. The photoelectric conversion film **217** converts incident light into an electric signal (charges).

The gate electrode **204B** included in the amplification transistor **222** is connected to a non-metal contact plug **210B**. The N-type diffusion region **205** is connected to a non-metal contact plug **210C**. The non-metal contact plugs **210B** and **210C** are connected to a metal line **214A**. That is, the gate electrode **204B** in the amplification transistor **222** and the N-type diffusion region **205** are electrically connected via the non-metal contact plugs **210B** and **210C** and the metal line **214A**. Moreover, the metal line **214A** is connected to the photoelectric conversion film **217** via a metal plug **215A**.

The N-type diffusion region **205** functions as a floating diffusion which holds charges generated in the photoelectric conversion film **217**.

Here, the relationship $H_r < D_f$ holds, where H_r represents the height of the gate electrode **204C** and D_f represents the junction depth of the N-type diffusion region **205**. That is, the junction depth D_f of the N-type diffusion region **205** is greater than the height H_r of the gate electrode **204C**. Here, in the present embodiment, thermal diffusion is performed to suppress a leakage current in PN junction between the N-type diffusion region **205** and the semiconductor substrate **201**. By so doing, the N-type diffusion region **205** is sufficiently expanded toward the surface of the semiconductor substrate **201**, and the junction depth becomes deeper as described above. Moreover, to suppress the leakage current in the PN junction, preferably, the impurity concentration of the N-type diffusion region **205** should be at most $1 \times 10^{19} \text{ cm}^{-3}$.

Moreover, the non-metal contact plugs **210B** and **210C** are, for example, polycrystal silicon containing impurities of the same conductivity type as the impurities of the N-type diffusion region **205**.

Moreover, the peripheral circuit unit **260** illustrated in FIG. 2 includes an NchMOS transistor **225** and a PchMOS transistor **226**. Moreover, the NchMOS transistor **225** and the PchMOS transistor **226** formed on the surface of the semiconductor substrate **201** are separated by the element isolation region **202**.

The NchMOS transistor **225** includes a P-well **231**, a gate insulating film **233D**, a gate electrode **204D**, sidewalls **209D**, N-type extension diffusion regions **234**, N-type source and drain diffusion regions **236**, and silicide films **238D** and **240D**. Here, the P-well **231** is formed on the surface of the semiconductor substrate **201**. The gate insulating film **233D** is formed above the semiconductor substrate **201**. The gate electrode **204D** is formed on the gate insulating film **233D**. The sidewalls **209D** are formed on the side faces of the gate electrode **204D**. The N-type extension diffusion regions **234** are formed on the surface of the semiconductor substrate **201**, on opposite sides of the gate electrode **204D**. The N-type source and drain diffusion regions **236** are formed on the semiconductor substrate **201**, one on either side of the sidewalls **209D** sandwiching the gate electrode **204D**. The silicide films **238D** and the silicide film **240D** are respectively formed on the surfaces of the N-type source and drain diffusion regions **236** and the gate electrode **204D**. The sidewall **209D** includes a silicon oxide film **207D** and a silicon nitride film **208D**.

The PchMOS transistor **226** includes an N-well **232**, a gate insulating film **233E**, a gate electrode **204E**, sidewalls **209E**, P-type extension diffusion regions **235**, P-type source and drain diffusion regions **237**, silicide films **238E** and **240E**. Here, the N-well **232** is formed on the semiconductor substrate **201**. The gate insulating film **233E** is formed above the semiconductor substrate **201**. The gate electrode **204E** is formed on the gate insulating film **233E**. The sidewalls **209E** are formed on the side faces of the gate electrode **204E**. The P-type extension diffusion regions **235** are formed on the semiconductor substrate **201**, on the opposite sides of the gate electrode **204E**. The P-type source and drain diffusion regions **237** are formed on the semiconductor substrate **201**, one on either side of the sidewalls **209E** sandwiching the gate electrode **204E**. The silicide films **238E** and the silicide film **240E** are respectively formed on the surfaces of the P-type source and drain diffusion regions **237** and the gate electrode **204E**. The sidewall **209E** includes a silicon oxide film **207E** and a silicon nitride film **208E**.

The silicide films **238D**, **238E**, **240D**, and **240E** are connected with metal contact plugs **239**. The metal contact plugs **239** are connected with metal lines **214D**, respectively.

Here, to reduce parasitic resistance in the sources and drains of the NchMOS transistor **225** and the PchMOS transistor **226** and improve the driving capabilities of the transistors, it is preferable that the impurity concentration of each of the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237** be at least $1 \times 10^{20} \text{ cm}^{-3}$.

Moreover, the relationships $H_n \geq D_n$ and $H_p \geq D_p$ hold, where H_n represents the height of the gate electrode **204D**, H_p represents the height of the gate electrode **204E**, D_n represents the junction depth of the N-type source and drain diffusion region **236**, and D_p represents the junction depth of the P-type source and drain diffusion region **237**. That is, the junction depth D_n of the N-type source and drain diffusion region **236** is at most the height H_n of the gate electrode **204D**.

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The junction depth D_p of the P-type source and drain diffusion region **237** is at most the height H_p of the gate electrode **204E**. Moreover, in the present embodiment, the expansion of the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237** due to the thermal diffusion of these layers is suppressed to improve the driving capabilities of the NchMOS transistor **225** and the PchMOS transistor **226**. This can decrease a gate length L_n of the NchMOS transistor **225** and a gate length L_p of the PchMOS transistor **226**. For instance, the driving capabilities of the MOS transistors can be improved by setting the gate lengths L_n and L_p to 65 nm or less.

As described above with reference to the drawings, the solid-state imaging device according to the present embodiment includes the pixel unit **250** and the peripheral circuit unit **260** formed at the periphery of the pixel unit **250**, both of which are formed on the semiconductor substrate **201**. The pixel unit **250** includes the photoelectric conversion film **217** which converts incident light into charges and a floating diffusion (the N-type diffusion region **205**) which holds the charges generated by the photoelectric conversion film **217**. The peripheral circuit unit **260** includes the NchMOS transistor **225** including the gate electrode **204D** and the two N-type source and drain diffusion regions **236** and the PchMOS transistor **226** including the gate electrode **204E** and the two P-type source and drain diffusion regions **237**. The impurity concentration of each of the two N-type source and drain diffusion regions **236** and the two P-type source and drain diffusion regions **237** is higher than the impurity concentration of the N-type diffusion region **205** (floating diffusion).

This can suppress the expansion of the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237**. Thus, the gate lengths of the NchMOS transistor **225** and the PchMOS transistor **226** can be decreased. Furthermore, it is possible to repair defects on the surface of the semiconductor substrate **201** due to damage caused by ion implantation to form the floating diffusion in the pixel unit **250**, thereby achieving the pixel characteristic of high sensitivity. That is, defects such as dangling bond can be reduced without performing, after forming the photoelectric conversion film **217**, the high temperature sintering treatment which results in characteristic degradation of the photoelectric conversion film **217** (the treatment is performed at, for example, a temperature of 400° C. or above). It should be noted that if the photoelectric conversion film **217** is formed with an organic material, the heat resistance of the film often becomes a problem. Thus, if the photoelectric conversion film **217** is formed with the organic material, advantageous effects of the present embodiment will become more obvious than the case where the photoelectric conversion film **217** is formed with an inorganic material. Another problem is degradation of the characteristics of the solid-state imaging device due to light reflection off the photoelectric conversion film **217**. The characteristic degradation can be mitigated by forming the photoelectric conversion film **217** with an organic material.

Moreover, the depths of the N-type source and drain diffusion region **236** and the P-type source and drain diffusion region **237** may be at most the heights of the gate electrodes **204D** and **204E**, respectively. This means that the expansion of the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237** is suppressed. Thus, the gate lengths of the NchMOS transistor **225** and the PchMOS transistor **226** in the peripheral circuit unit **260** can be decreased.

Moreover, the depth of the floating diffusion (the N-type diffusion region **205**) may be at least the heights of the gate

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electrodes **204A** to **204C**. This means that the floating diffusion is sufficiently diffused. Thus, gradual expansion of the floating diffusion can suppress a leakage current in the PN junction. This can improve the sensitivity of a pixel.

Moreover, the impurity concentration of each of the N-type source and drain diffusion regions **236** in the NchMOS transistor **225** and the P-type source and drain diffusion regions **237** in the PchMOS transistor **226** may be at least $1 \times 10^{20} \text{ cm}^{-3}$. By so doing, the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237** have low resistance. Thus, the driving capabilities of the NchMOS transistor **225** and the PchMOS transistor **226** can be improved.

Moreover, the impurity concentration of the floating diffusion (the N-type diffusion region **205**) may be at most $1 \times 10^{19} \text{ cm}^{-3}$. This can gradually expand the floating diffusion.

Moreover, the lengths of the gate electrodes **204D** and **204E** respectively in the NchMOS transistor **225** and the PchMOS transistor **226** may be 65 nm or less. This can improve the driving capabilities of the NchMOS transistor **225** and the PchMOS transistor **226** in the peripheral circuit unit **260**.

Moreover, the floating diffusion (the N-type diffusion region **205**) may be connected with the photoelectric conversion film **217** via the non-metal contact plug **210C** and the metal line **214A** by connecting the non-metal contact plug **210C** to the floating diffusion. This can achieve lower contact resistance between the floating diffusion and the contact plug than the case where a contact plug of general metal such as tungsten is used.

It should be noted that the solid-state imaging device according to the present embodiment is not limited to the above configuration, and the present disclosure is applicable to solid-state imaging devices having other configurations. For instance, in the above example, the present disclosure is applied to the solid-state imaging device in which a photoelectric conversion film is used as a photoelectric conversion unit. However, the present disclosure may be applied to a solid-state imaging device which includes a photodiode having a buried diffusion region formed in a semiconductor substrate.

Moreover, in the above description, the transistors included in the pixel unit **250** are Nch transistors. However, a part or all of the transistors may be Pch transistors.

Moreover, in the above description, the peripheral circuit unit **260** includes the NchMOS transistor **225** and the PchMOS transistor **226**. However, the peripheral circuit unit **260** may include either the NchMOS transistor **225** or the PchMOS transistor **226**.

Moreover, an implant isolation region may be used as the element isolation region **202**, instead of a STI region. By so doing, it is possible to decrease a leakage current due to crystal defects on the interface between the STI region and the semiconductor substrate.

Moreover, the metal line layer in the above example is a single layer. However, the metal line layer may have a multi-layer interconnect structure.

With reference to FIGS. **3** to **20**, the following describes a method of manufacturing the solid-state imaging device according to the present embodiment. FIGS. **3**, **5**, **7**, **9**, **11**, **13**, **15**, **17**, and **19** are cross-sectional views of the pixel unit **250** in a manufacturing process of the solid-state imaging device according to the present embodiment. Moreover, FIGS. **4**, **6**, **8**, **10**, **12**, **14**, **16**, **18**, and **20** are cross-sectional views of the peripheral circuit unit **260** in the manufacturing process of the solid-state imaging device according to the present embodiment.

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As FIGS. 3 and 4 illustrate, the element isolation regions **202** are formed on the surface of the semiconductor substrate **201**. Here, the element isolation region **202** is formed in the pixel unit **250** so as to separate an amplification transistor region where the amplification transistor **222** is to be formed, from a reset transistor region where the reset transistor **223** is to be formed. Here, the element isolation region **202** may be formed so as to separate a select transistor region where the select transistor **221** is to be formed, from the amplification transistor region. At the same time, as FIG. 4 illustrates, the element isolation region **202** is formed so as to separate an NchMOS transistor region where the NchMOS transistor **225** is to be formed, from a PchMOS transistor region where the PchMOS transistor **226** is to be formed.

As FIG. 4 illustrates, the P-well **231** is formed by ion implantation, on the surface of the semiconductor substrate **201** in the NchMOS transistor region of the peripheral circuit unit **260**. The N-well **232** is formed by the ion implantation, on the surface of the semiconductor substrate **201** in the PchMOS transistor region.

As FIG. 5 illustrates, a gate oxide film and a polycrystal silicon film are formed in the stated order on the surface of the semiconductor substrate **201** in the select transistor region, the amplification transistor region, and the reset transistor region of the pixel unit **250**. These gate oxide film and polycrystal silicon film are patterned into desired shapes. Thus, the gate insulating film **203A** and the gate electrode **204A** are formed in the select transistor region. The gate insulating film **203B** and the gate electrode **204B** are formed in the amplification transistor region. The gate insulating film **203C** and the gate electrode **204C** are formed in the amplification transistor region.

Moreover, as FIG. 6 illustrates, the gate insulating film and the polycrystal silicon film are formed in the stated order on the surface of the semiconductor substrate **201** in the NchMOS transistor region and the PchMOS transistor region of the peripheral circuit unit **260**. These gate oxide film and polycrystal silicon film are patterned into desired shapes. Thus, the gate insulating film **233D** and the gate electrode **204D** are formed in the NchMOS transistor region. The gate insulating film **233E** and the gate electrode **204E** are formed in the PchMOS transistor region.

Here, for instance, the gate oxide films are formed in the same process in the select transistor region, the amplification transistor region, and the reset transistor region of the pixel unit **250**. It should be noted that if the transistors have different film thicknesses, the gate oxide films may be formed in separate processes in the respective regions. Moreover, for instance, the gate oxide films are formed in the same process in the NchMOS transistor region and the PchMOS transistor region of the peripheral circuit unit **260**.

Moreover, the polycrystal silicon films are formed in the same process in the pixel unit **250** and the peripheral circuit unit **260**. Here, the polycrystal silicon films have a film thickness of 120 nm, for example. Moreover, the gate oxide films and the polycrystal silicon films are patterned into the desired shapes in the same process in the pixel unit **250** and the peripheral circuit unit **260**.

Here, the length L_n of the gate electrode **204D** of the NchMOS transistor **225** and the length L_p of the gate electrode **204E** of the PchMOS transistor **226** in the peripheral circuit unit **260** are the gate lengths of the MOS transistors, respectively. Moreover, preferably, the minimum gate length of each of the MOS transistors should be 65 nm or less. This can improve the driving capabilities of the MOS transistors.

As FIG. 7 illustrates, a resist **241** is patterned in the pixel unit **250** so as to expose a portion of the surface of the

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semiconductor substrate **201** in the reset transistor region. The ion implantation selectively forms an N-type diffusion region **205A** on the surface of the semiconductor substrate **201**, on one side of the gate electrode **204C**. A condition for the ion implantation is, for example, that ions do not pass through the gate electrode **204C** to the surface of the semiconductor substrate **201** under the gate insulating film **203C**.

Moreover, preferably, a small implantation dosage of ions should be set to suppress defects due to damage caused by the ion implantation. Conditions here for the ion implantation are, for example, that phosphorus is used for a dopant (impurity), implantation energy is 30 keV, and a dosage is 1×10^{11} to $1 \times 10^{13} \text{ cm}^{-2}$. Here, as FIG. 8 illustrates, the entire exposed surface of the peripheral circuit unit **260** is covered by a resist **241**.

As FIGS. 9 and 10 illustrate, a heat treatment is performed using a diffusion furnace. Thus, the N-type diffusion region **205A** is thermally diffused to form the N-type diffusion region **205**. Here, the N-type diffusion region **205** is a floating diffusion which holds an electric signal generated by the photoelectric conversion unit **224** converting incident light. Moreover, this heat treatment repairs defects due to damage caused by the ion implantation to form the N-type diffusion region **205** in the pixel unit **250**. Furthermore, this thermal diffusion makes a gentle impurity profile of the N-type diffusion region **205**, thereby suppressing a leakage current in the PN junction between the N-type diffusion region **205** and the semiconductor substrate **201**. Conditions for the heat treatment are, for example, a temperature of 800° C. to 900° C. and duration within 120 minutes.

Moreover, sufficient diffusion of the N-type diffusion region **205** by the thermal diffusion sufficiently deepens the N-type diffusion region **205**. As a result, the relationship $H_r < D_f$ holds, where H_r represents the height of the gate electrode **204C** and D_f represents the depth of the N-type diffusion region **205** after the heat treatment.

As FIG. 11 illustrates, a resist **242** is patterned in the pixel unit **250** so as to expose portions of the surface of the semiconductor substrate **201** other than a portion of the surface corresponding to the N-type diffusion region **205**. The ion implantation selectively forms in the same process on the surface of the semiconductor substrate **201**, the N-type diffusion regions **206A**, **206B**, **206C**, and **206D**. Here, the N-type diffusion regions **206A** and **206B** are formed on opposite sides of the gate electrode **204A** in the select transistor region. The N-type diffusion regions **206B** and **206C** are formed on opposite sides of the gate electrode **204B** in the amplification transistor region. The N-type diffusion region **206D** is formed on one side of the gate electrode **204C** in the reset transistor region that is the side on which the N-type diffusion region **205** is formed. The N-type diffusion region **206D** faces the N-type diffusion region **205** across the gate electrode **204C**.

Conditions for the ion implantation are, for example, that phosphorus is used for a dopant, implantation energy is 20 keV, and a dosage is 1×10^{12} to $1 \times 10^{14} \text{ cm}^{-2}$. Here, if it is preferable that the N-type diffusion regions **206A**, **206B**, and **206C** be separately formed, resists having openings respectively corresponding to the N-type diffusion regions are sequentially patterned and the respective N-type diffusion regions are formed under different implantation conditions. Here, as FIG. 12 illustrates, the entire exposed surface of the peripheral circuit unit **260** is covered by the resist **242**. Moreover, the ion implantation may be performed before the heat treatment in FIGS. 9 and 10.

As FIGS. 13 and 14 illustrate, in the NchMOS transistor region in the peripheral circuit unit **260**, the ion implantation forms two N-type extension diffusion regions **234A** on the

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surface of the semiconductor substrate **201**, on opposite sides of the gate electrode **204D**. Subsequently, the ion implantation forms two P-type extension diffusion regions **235A** on the surface of the semiconductor substrate **201**, on opposite sides of the gate electrode **204E** in the PchMOS transistor region. Here, conditions for the ion implantation to form the N-type extension diffusion regions **234A** are, for example, that arsenic is used for a dopant, implantation energy is 5 keV, and a dosage is 1×10^{14} to 1×10^{15} cm⁻². Moreover, conditions for the ion implantation to form the P-type extension diffusion regions **235A** are, for example, that boron is used for a dopant, implantation energy is 1 keV, and a dosage is 1×10^{14} to 1×10^{15} cm⁻².

As FIGS. **15** and **16** illustrate, silicon oxide films and silicon nitride films are formed in the stated order on the surface of the semiconductor substrate **201**. By dry-etching these silicon oxide films and silicon nitride films, the sidewalls **209A**, **209B**, **209C**, **209D**, and **209E** are formed in the same process. Here, the sidewalls **209A** are formed on the side faces of the gate electrode **204A** in the select transistor region, and each include the silicon oxide film **207A** and the silicon nitride film **208A**. The sidewalls **209B** are formed on the side faces of the gate electrode **204B** in the amplification transistor region, and each include the silicon oxide film **207B** and the silicon nitride film **208B**. The sidewalls **209C** are formed on the side faces of the gate electrode **204C** in the reset transistor region, and each include the silicon oxide film **207C** and the silicon nitride film **208C**. The sidewalls **209D** are formed on the side faces of the gate electrode **204D** in the NchMOS transistor region, and each include the silicon oxide film **207D** and the silicon nitride film **208D**. The sidewalls **209E** are formed on the side faces of the gate electrode **204E** in the PchMOS transistor region, and each include the silicon oxide film **207E** and the silicon nitride film **208E**.

The N-type source and drain diffusion regions **236** are selectively formed by the ion implantation, one on either side of the sidewalls **209D** sandwiching the gate electrode **204D**. Moreover, the two P-type source and drain diffusion regions **237** are selectively formed by the ion implantation, one on either side of the sidewalls **209E** sandwiching the gate electrode **204E**. Moreover, the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237** are formed on the surface of the semiconductor substrate **201**.

A heat treatment is performed using a lamp annealing apparatus. This activates impurities in the N-type diffusion regions **206A**, **206B**, **206C**, and **206D** in the pixel unit **250** and impurities in the N-type and P-type extension diffusion regions **234** and **235** and the N-type and P-type source and drain diffusion regions **236** and **237** in the peripheral circuit unit **260**. Here, for example, a silicon oxide film having a film thickness of 5 nm to 20 nm is formed using a chemical vapor deposition (CVD) apparatus. Moreover, a silicon nitride film having a film thickness of 30 nm to 60 nm is formed using the CVD apparatus or an atomic layer deposition (ALD) apparatus.

Here, a condition for the ion implantation to form the N-type and P-type source and drain diffusion regions **236** and **237** is, for example, that ions do not pass through the gate electrode **204D** and the gate electrode **204E** to the surface of the semiconductor substrate **201** under the gate insulating film **233D** and the gate insulating film **233E**. Conditions for the ion implantation to form the N-type source and drain diffusion regions **236** are, for example, that arsenic is used for a dopant, implantation energy is 30 keV, and a dosage is 1×10^{15} to 1×10^{16} cm⁻². Moreover, conditions for the ion implantation to form the P-type source and drain diffusion regions **237**

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are, for example, that boron is used for a dopant, implantation energy is 5 keV, and a dosage is 1×10^{15} to 1×10^{16} cm⁻². Moreover, conditions for the heat treatment are, for example, a temperature of 900° C. or above and duration of 5 seconds or less or spike (0 second).

These conditions for the heat treatment can concurrently (i) activate impurities in the N-type extension diffusion regions **234**, the P-type extension diffusion regions **235**, the N-type source and drain diffusion regions **236**, and the P-type source and drain diffusion regions **237** in the peripheral circuit unit **260** and (ii) suppress the thermal diffusion of each diffusion region. Thus, the gate length of the transistors of the peripheral circuit unit **260** can be decreased, thereby improving the driving capabilities of the NchMOS transistor **225** and the PchMOS transistor **226** in the peripheral circuit unit **260**.

Moreover, the treatments of a rapid temperature rise and drop are performed in the heat treatment using the lamp annealing apparatus. Thus, there is a possibility that more dangling bonds are seen on the interfaces between the semiconductor substrate **201** and the gate insulating films **203A**, **203B**, **203C**, **233D**, and **233E**. The dangling bonds may degrade pixel characteristics by resulting in a leakage source especially in the amplification transistor **222**. To decrease the dangling bonds, the heat treatment may be performed by the diffusion furnace after the heat treatment is performed by the lamp annealing apparatus. It should be noted that it is necessary to decrease the thermal diffusion as much as possible of the N-type extension diffusion regions **234**, the P-type extension diffusion regions **235**, the N-type source and drain diffusion regions **236**, and the P-type source and drain diffusion regions **237** in the peripheral circuit unit **260**. Thus, preferably, a temperature during the heat treatment performed in the diffusion furnace should be as low as possible. Conditions for the heat treatment are, for example, a temperature of 700° C. to 800° C. and duration within 15 minutes.

Through the above process, the impurity concentration of the N-type diffusion region **205** is at most 1×10^{19} cm⁻³. The impurity concentration of each of the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237** is at least 1×10^{20} cm⁻³. That is, the impurity concentration of each of the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237** is higher than the impurity concentration of the N-type diffusion region **205** (floating diffusion).

As FIGS. **17** and **18** illustrate, the silicide films **238D**, **240D**, **238E**, and **240E** are respectively formed on the surfaces of the N-type source and drain diffusion regions **236**, the top surface of the gate electrode **204D**, the surfaces of the P-type source and drain diffusion regions **237**, and the top surface of the gate electrode **204E** in the peripheral circuit unit **260**. Here, a silicide block film **218** formed of a silicon oxide film is formed in the pixel unit **250**. This can prevent silicide from being formed in the pixel unit **250**. The prevention of silicide from being formed in the pixel unit **250** can prevent a metal atom from reaching the N-type diffusion region **205** as a floating diffusion and resulting in a leakage current source. This can improve pixel characteristics.

As FIG. **19** illustrates, an interlayer insulating film **213A** is formed in the pixel unit **250**. Holes are formed so that a portion of the surface of the gate electrode **204B** and a portion of the surface of the N-type diffusion region **205** are exposed. The non-metal contact plugs **210B** and **210C** are formed in the holes above. The metal line **214A** for connecting the non-metal contact plugs **210B** and **210C** are formed. An interlayer insulating film **216A** is formed. A hole is formed in the interlayer insulating film **216A** so that a portion of the metal line **214A** is exposed. The metal plug **215A** is formed in

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the above hole. The photoelectric conversion film **217** is formed on the metal plug **215A**.

Here, the photoelectric conversion film **217** is a photoelectric conversion unit which converts incident light into an electric signal. Moreover, an interlayer insulating film **213D** is formed in the peripheral circuit unit **260**. Holes are formed in the interlayer insulating film **213D** so that a portion of each surface of the silicide films **238D**, **238E**, **240D**, and **240E** is exposed. The metal contact plugs **239** including tungsten are formed in the above holes, for example. The metal lines **214D** respectively connecting with the non-metal contact plugs **239** are formed. An interlayer insulating film **216D** is formed.

Here, the interlayer insulating film **213A** in the pixel unit **250** and the interlayer insulating film **213D** in the peripheral circuit unit **260** may be concurrently formed. Moreover, the interlayer insulating film **216A** in the pixel unit **250** and the interlayer insulating film **216D** in the peripheral circuit unit **260** may be concurrently formed. Moreover, the material of the non-metal contact plug **210C** is, for example, polycrystal silicon containing impurities of the same conductivity type as the impurities of the N-type diffusion region **205**. Here, the impurity concentration of the N-type diffusion region **205** is relatively low. Thus, the use of a metal material such as tungsten for the contact plug increases a contact resistance between the N-type diffusion region **205** and the contact plug. In contrast, the use of a non-metal contact plug can decrease a contact resistance between the N-type diffusion region **205** and the contact plug.

As described with reference to the drawings, a method of manufacturing a solid-state imaging device according to the present embodiment is a method of manufacturing a solid-state imaging device including: a pixel unit **250** formed on the semiconductor substrate **201** and a peripheral circuit unit **260** formed on the semiconductor substrate **201**, at the periphery of the pixel unit **250**. The pixel unit **250** includes: the photoelectric conversion film **217** which converts incident light into charges and a floating diffusion (the N-type diffusion region **205**) which holds the generated charges. The peripheral circuit unit **260** includes: the NchMOS transistor **225** including the gate electrode **204D** and the two N-type source and drain diffusion regions **236** and the PchMOS transistor **226** including the gate electrode **204E** and the two P-type source and drain diffusion regions **237**. A method of manufacturing the solid-state imaging device includes steps (a) to (g). In step (a), the gate electrodes **204A** to **204E** are formed above the semiconductor substrate **201** in the pixel unit **250** and the peripheral circuit unit **260**. In step (b), a first impurity is implanted into the surface of the semiconductor substrate **201** in the pixel unit **250** after step (a) to form a floating diffusion (the N-type diffusion region **205**). In step (c), a first heat treatment is performed after step (b). In step (d), a second impurity is implanted into the surface of the semiconductor substrate **201** in the peripheral circuit unit **260** after step (c) to form diffusion regions having a low impurity concentration (the N-type extension diffusion regions **234**/the P-type extension diffusion regions **235**) to be included in two source and drain diffusion regions. In step (e), the sidewalls **209D** and **209E** are formed on the side faces of the gate electrodes **204D** and **204E** after step (d). In step (f), a third impurity is implanted into the surface of the surface of the peripheral circuit unit **260** after step (e) to form diffusion regions having a high concentration (N-type source and drain diffusion regions **236**/the P-type source and drain diffusion regions **237**) to be included in two source and drain diffusion regions. In step (g), a second heat treatment is performed after step (f).

This allows the method of manufacturing a solid-state imaging device according to the present embodiment to

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reduce defects due to damage caused by ion implantation, by performing the first heat treatment on the floating diffusion. Moreover, the method of manufacturing can suppress the expansion of the N-type source and drain diffusion regions **236** and the P-type source and drain diffusion regions **237** in the peripheral circuit unit **260** by properly setting the conditions for the second heat treatment. Thus, the gate lengths of the NchMOS transistor **225** and the PchMOS transistor **226** can be decreased. Thus, the method of manufacturing can achieve both of miniaturization of the transistors included in the peripheral circuit unit **260** and reduction of defects due to damage caused by the ion implantation to form the floating diffusion in the pixel unit **250**.

Moreover, the first heat treatment may be performed at a temperature of 800° C. or above using a diffusion furnace. This can repair defects on the surface of the semiconductor substrate **201** in the pixel unit **250** due to damage caused by the ion implantation in step (b).

Moreover, the second heat treatment may be performed at a temperature of 900° C. or above using a lamp annealing apparatus. This can achieve both of activation and suppression of thermal expansion of the second impurities and the third impurities implanted into the surface of the semiconductor substrate **201** of the peripheral circuit unit **260**. This can decrease the gate lengths of the NchMOS transistor **225** and the PchMOS transistor **226** in the peripheral circuit unit **260**.

Moreover, the method of manufacturing a solid-state imaging device according to the present embodiment may further include (h) forming the non-metal contact plug **210C** in the pixel unit **250** after step (g). This can achieve a lower contact resistance between the floating diffusion and the contact plug than the case where a contact plug of general metal such as tungsten is used.

Moreover, the non-metal contact plug **210C** may be polycrystal silicon containing impurities.

Moreover, the method of manufacturing a solid-state imaging device according to the present embodiment may further include performing a third heat treatment using a diffusion furnace after step (h), in which the third heat treatment may be performed at a temperature which is at most a temperature during the first heat treatment. This can decrease dangling bonds caused on the interfaces between the semiconductor substrate **201** and the gate insulating films **203A** to **203C** in the pixel unit **250** when a lamp annealing apparatus is used in the second heat treatment. Moreover, a temperature during the third heat treatment is at most a temperature during the first heat treatment. Thus, it is possible to suppress thermal diffusion of the second impurities implanted into the surface of the semiconductor substrate **201** in the peripheral circuit unit **260**. This can decrease the gate lengths of the NchMOS transistor **225** and the PchMOS transistor **226** of the peripheral circuit unit **260**.

The solid-state imaging device and the method of manufacturing the solid-state imaging device according to the present embodiment are described above. However, the present disclosure is not limited to the present embodiment.

Moreover, the process units included in the solid-state imaging device according to the present embodiment are typically achieved as large scale integration (LSI) which is an integrated circuit. These process units may become separate chips, or a part or all of the process units may form one chip.

Moreover, in the above cross-sectional views and others, the corners and the sides of the structural elements are linearly drawn. However, the present disclosure also includes round corners and curved sides for manufacturing reasons.

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Moreover, the functions of the solid-state imaging device according to the embodiment and its modifications may be at least partially combined.

The above numerals are used to exemplify the entirety of the present disclosure in detail. Thus, the present disclosure is not limited to the exemplified numerals. Moreover, for example, the N-type and P-type are set for transistors and others to exemplify the present disclosure in detail. However, even if the N-type and P-type are reversely set, the same result can be achieved. Moreover, the above materials of the structural elements are used to exemplify the entirety of the present disclosure in detail. Thus, the present disclosure is not limited to the materials exemplified above. Moreover, the connections between the structural elements are used to exemplify the present disclosure in detail. Thus, connections for achieving the functions of the present disclosure are not limited to the above connections.

Furthermore, modifications obtained by making changes which those skilled in the art would conceive to the present embodiment are also included in the present disclosure unless the modifications do not depart from the scope of the present disclosure.

The herein disclosed subject matter is to be considered descriptive and illustrative only, and the appended Claims are of a scope intended to cover and encompass not only the particular embodiment disclosed, but also equivalent structures, methods, and/or uses.

INDUSTRIAL APPLICABILITY

The present disclosure is applicable to a solid-state imaging device. Moreover, the present disclosure is effectively used in, for example, a small image pickup apparatus for video shooting.

The invention claimed is:

1. A solid-state imaging device comprising:

a semiconductor substrate;

a pixel; and

a peripheral circuit at a periphery of the pixel, wherein the pixel includes:

a photoelectric conversion film which converts incident light into charges; and

a floating diffusion, in the semiconductor substrate, for holding the charges,

a non-metal contact plug connected with the floating diffusion,

a line connected with the non-metal contact plug, the floating diffusion and the photoelectric conversion film being connected to each other via the non-metal contact plug and the line,

the peripheral circuit includes

a transistor including a gate electrode and source and drain diffusion regions, the source and drain diffusion regions located in the semiconductor substrate, and the source and drain diffusion regions each have a higher impurity concentration than an impurity concentration of the floating diffusion.

2. The solid-state imaging device according to claim 1, wherein depths of the source and drain diffusion regions are at most a height of the gate electrode.

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3. The solid-state imaging device according to claim 1, wherein a depth of the floating diffusion is at least a height of the gate electrode.

4. The solid-state imaging device according to claim 2, wherein a depth of the floating diffusion is at least a height of the gate electrode.

5. The solid-state imaging device according to claim 1, wherein the source and drain diffusion regions each have an impurity concentration of at least $1 \times 10^{20} \text{ cm}^{-3}$.

6. The solid-state imaging device according to claim 1, wherein the floating diffusion has an impurity concentration of at most $1 \times 10^{19} \text{ cm}^{-3}$.

7. The solid-state imaging device according to claim 1, wherein a gate length of the gate electrode is 65 nm or less.

8. The solid-state imaging device according to claim 1, wherein the photoelectric conversion film includes an organic material.

9. The solid-state imaging device according to claim 1, wherein the line is directly connected with the non-metal contact plug.

10. The solid-state imaging device according to claim 1, wherein the non-metal contact plug is directly connected with the floating diffusion.

11. A solid-state imaging device comprising:

a semiconductor substrate;

a pixel; and

a peripheral circuit at a periphery of the pixel, wherein the pixel includes:

a photoelectric conversion film which converts incident light into charges; and

a floating diffusion, in the semiconductor substrate, for holding the charges,

a non-metal connector directly connected with the floating diffusion, and electrically coupled to the photoelectric conversion film,

a transistor including a gate electrode and source and drain diffusion regions, the source and drain diffusion regions located in the semiconductor substrate, and the source and drain diffusion regions each have a higher impurity concentration than an impurity concentration of the floating diffusion.

12. The solid-state imaging device according to claim 11, wherein depths of the source and drain diffusion regions are at most a height of the gate electrode.

13. The solid-state imaging device according to claim 11, wherein a depth of the floating diffusion is at least a height of the gate electrode.

14. The solid-state imaging device according to claim 12, wherein a depth of the floating diffusion is at least a height of the gate electrode.

15. The solid-state imaging device according to claim 11, wherein the source and drain diffusion regions each have an impurity concentration of at least $1 \times 10^{20} \text{ cm}^{-3}$.

16. The solid-state imaging device according to claim 11, wherein the floating diffusion has an impurity concentration of at most $1 \times 10^{19} \text{ cm}^{-3}$.

17. The solid-state imaging device according to claim 11, wherein a gate length of the gate electrode is 65 nm or less.

18. The solid-state imaging device according to claim 11, wherein the photoelectric conversion film includes an organic material.

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